RoHS

COMPLIANT HALOGEN

FREE

Vishay Semiconductors

Hyperfast Rectifier, 4 A FRED Pt®



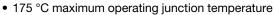


SMC (DO-214AB)

PRIMARY CHARACTERISTICS				
I _{F(AV)}	4 A			
V_{R}	600 V			
V _F at I _F	1.15 V			
t _{rr} typ.	30 ns			
T _J max.	175 °C			
Package	SMC (DO-214AB)			
Circuit configuration	Single			

FEATURES

 Hyperfast recovery time, reduced Q_{rr} and soft recovery



- For PFC CRM/CCM, snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		600	V	
Average rectified forward current	I _{F(AV)}	$T_L = 99 ^{\circ}C^{(1)}$	4	۸	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	90	Α	
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C	

Note

⁽¹⁾ Mounted on PCB with minimum pad size

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	.,
Femurard voltage	I _F = 4 A	-	1.6	1.85	V	
Forward voltage	V _F	I _F = 4 A, T _J = 150 °C	-	1.15	1.35	
Reverse leakage current I _R	1	V _R = V _R rated	-	-	3	
	IR IR	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	-	100	μA
Junction capacitance	C _T	V _R = 600 V	-	7.8	-	pF



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	30	-	
Reverse recovery time		$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	35	-	ns
	t _{rr}	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	35	
		T _J = 25 °C		-	22	-	
		T _J = 125 °C		-	37	-	
Peak recovery current I _{RRM}	1	T _J = 25 °C	$I_F = 4 A$ $dI_F/dt = 200 A/\mu s$	-	3.4	-	А
	IRRM	T _J = 125 °C	$V_{R} = 390 \text{ V}$	-	5.2	-	A
Reverse recovery charge	$Q_{rr} \qquad \frac{T_J = 25 \text{ °C}}{T_J = 125 \text{ °C}}$	T _J = 25 °C		-	38	-	nC
		T _J = 125 °C		-	104	-	110

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to case	R _{thJC} ⁽¹⁾		-	-	14	°C/W
Thermal resistance, junction to ambient	R _{thJA} (1)		-	-	80	C/VV
Approximate Weight				0.24		g
Approximate Weight			0.008		OZ.	
Marking device		Case style SMC (DO-214AB)		41	1 6	

Note

⁽¹⁾ Mounted on PCB with minimum pad size

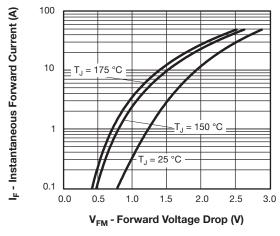


Fig. 1 - Typical Forward Voltage Drop Characteristics

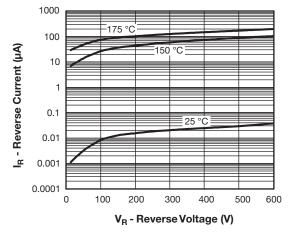


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

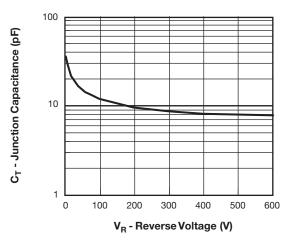


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

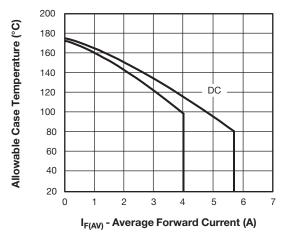


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

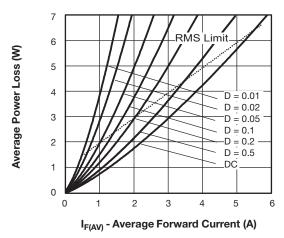


Fig. 5 - Forward Power Loss Characteristics

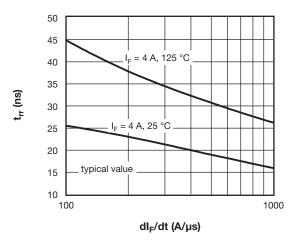


Fig. 6 - Typical Reverse Recovery vs. dI_F/dt

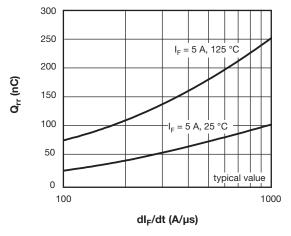
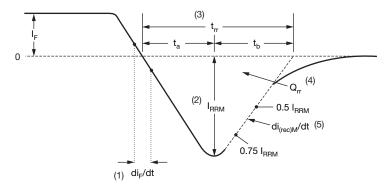


Fig. 7 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

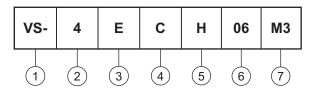
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- 2 Current rating (4 = 4 A)
- 3 Circuit configuration:

E = single diode

- C = SMC package
- 5 Process type,

H = hyperfast recovery

- 6 Voltage code (06 = 600 V)
- 7 M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-4ECH06-M3/9AT	9AT	3500	13"diameter plastic tape and reel		

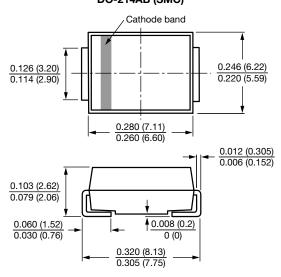
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95402			
Part marking information	www.vishay.com/doc?95472			
Packaging information	www.vishay.com/doc?95404			



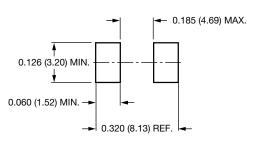
SMC

DIMENSIONS in inches (millimeters)

DO-214AB (SMC)



Mounting Pad Layout





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Vishay

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